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(54) Title: PLATING APPARATUS FOR METALLIZATION ON SEMICONDUCTOR WORKPIECE

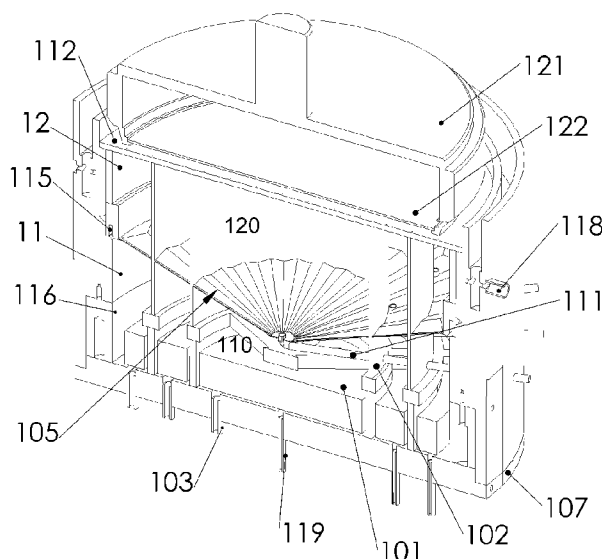


FIG 1a

(57) Abstract: The present invention provides a plating apparatus with multiple anode zones and cathode zones. The electrolyte flow field within each zone is controlled individually with independent flow control devices. A gas bubble collector whose surface is made into pleated channels is implemented for gas removal by collecting small bubbles, coalescing them, and releasing the residual gas. A buffer zone built within the gas bubble collector further allows unstable microscopic bubbles to dissolve.

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